Features

- Uses CRM(CQ) advanced Trench technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g x R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

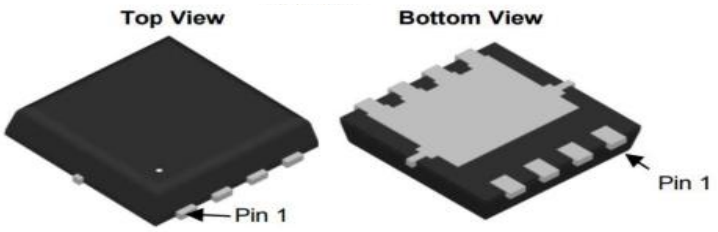
V_{DS}	30V
$R_{DS(on).typ}$	4.6mΩ
I_D	58A

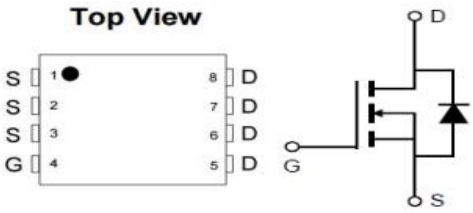
100% DVDS Tested
100% Avalanche Tested

Applications

- DC/DC Converter
- PWM Application
- high-frequency switching and synchronous rectification

PDFN3.3×3.3





CRTK050N03L4

Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTK050N03L4	050N03	PDFN3.3×3.3	Tape&Reel	N/A	N/A	5000

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	30	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 100°C (Silicon limit)	I_D	 58 37	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	232	A
Avalanche energy, single pulse (I_D = 18A, Rg=25Ω)[1]	E_{AS}	81	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	31	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	Tsold	260	°C

※. Notes:
1.EAS is tested at starting Tj = 25℃, L = 0.5mH, IAS =18A, VGS = 10V. The parameter is not subject to production testing-specified by design.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	4.0	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	42.5	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	30	-	-	V	V_{GS}=0V, I_D=250uA
		30	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{GS(th)}$	1.0	1.4	2.0	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=30V,V_{GS}=0V
		-	-	100		T_j=125°C
Gate-source leakage current	I_{GSS}	0	-	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	4.6	5.5	mΩ	VGS=10V, ID=19A
		-	6.2	7.8		VGS=4.5V, ID=19A
Transconductance	g_{fs}	-	72.0	-	S	V_{DS}=5V, I_D=19A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	1531	-	pF	V_{GS}=0V, V_{DS}=15V, f=1MHz
Output Capacitance	C_{oss}	-	146	-		
Reverse Transfer Capacitance	C_{rss}	-	164	-		
Gate Total Charge	Q_G	-	36.2	-	nC	V_{GS}=10V, V_{DS}=15V, I_D=19A
Gate-Source charge	Q_{gs}	-	6.6	-		
Gate-Drain charge	Q_{gd}	-	6.4	-		
Turn-on delay time	$t_{d(on)}$	-	6.0	-	ns	V_{GS}=10V, V_{DD}=15V, R_{G_ext}=2.7Ω
Rise time	t_r	-	26.8	-		
Turn-off delay time	$t_{d(off)}$	-	31.0	-		
Fall time	t_f	-	9.6	-		
Gate resistance	R_G	-	1.6	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.82	1.4	V	V_{GS}=0V,I_{SD}=19A
Body Diode Reverse Recovery Time	t_{rr}	-	9.3	-	ns	I_F=19A,dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	2.7	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

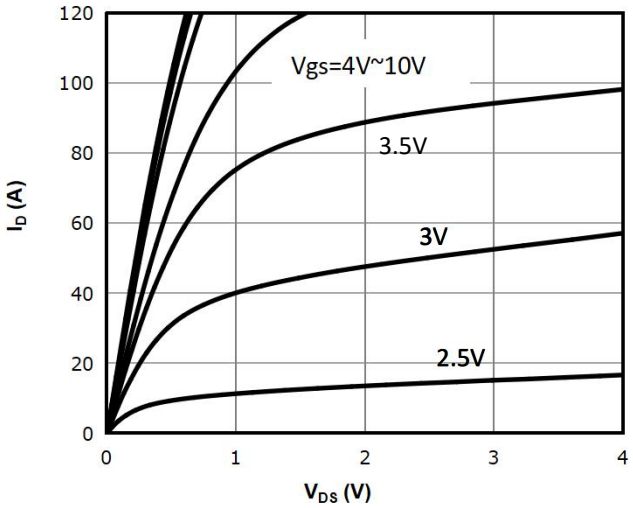


Fig 2: Transfer Characteristics

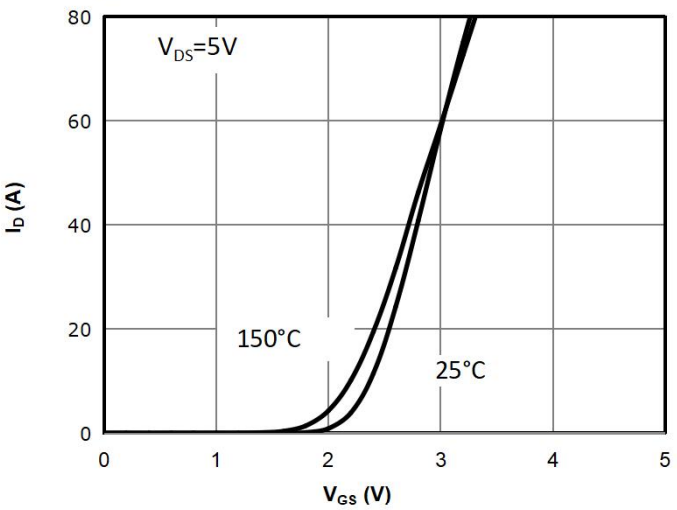


Fig 3: Rds(on) vs Drain Current and Gate Voltage

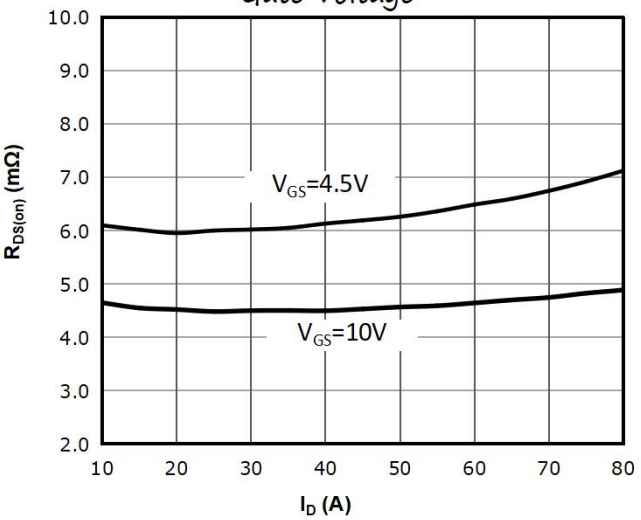


Fig 4: Rds(on) vs Gate Voltage

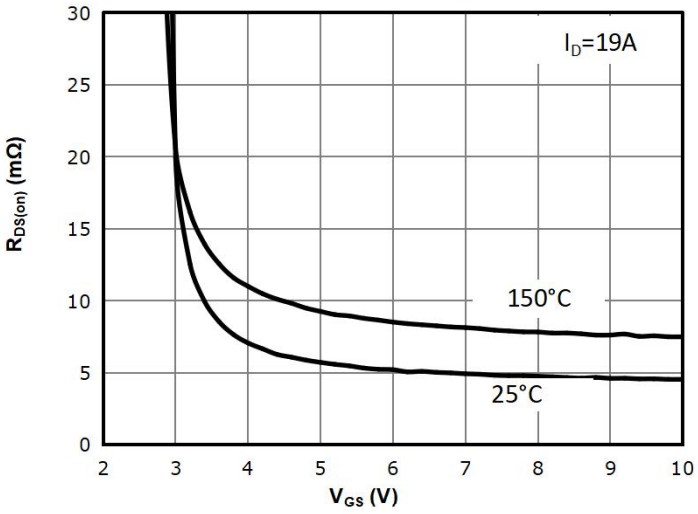


Fig 5: Rds(on) vs. Temperature

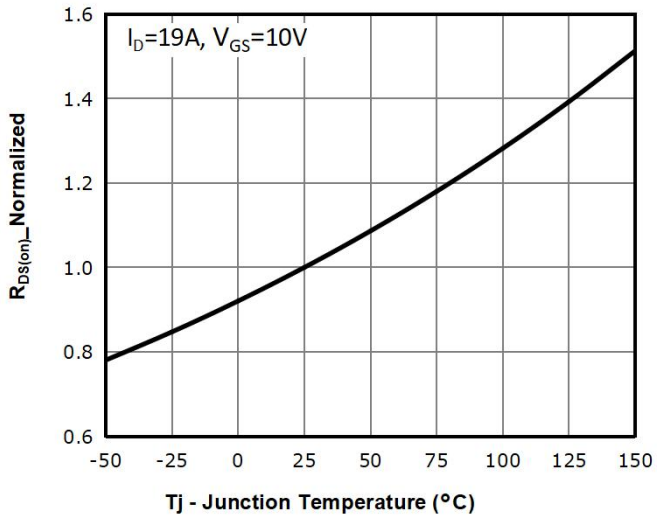


Fig 6: Vgs(th) vs. Temperature

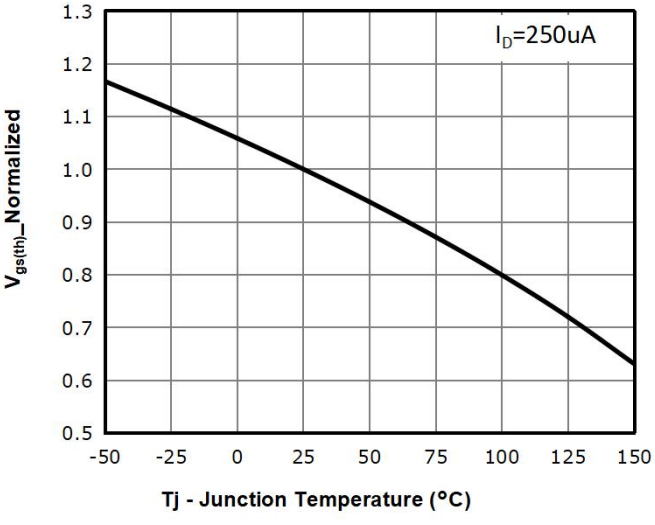


Fig 7: BVdss vs. Temperature

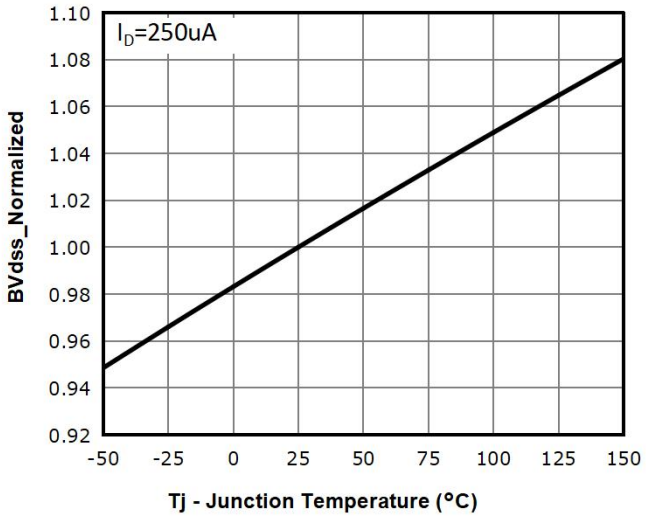


Fig 8: Capacitance Characteristics

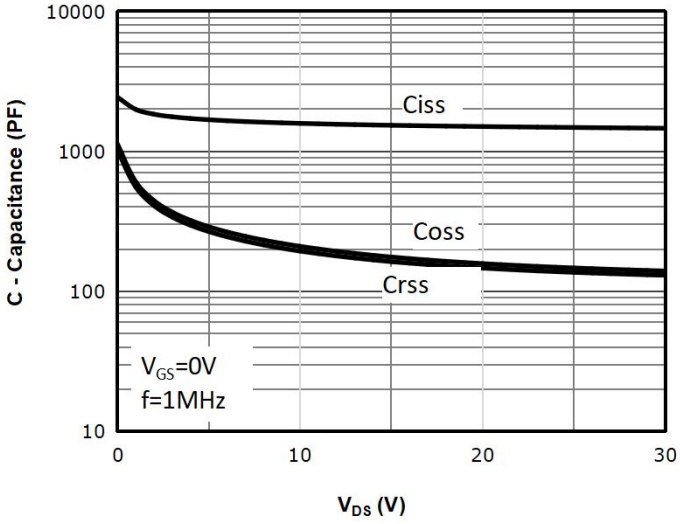


Fig 9: Gate Charge Characteristics

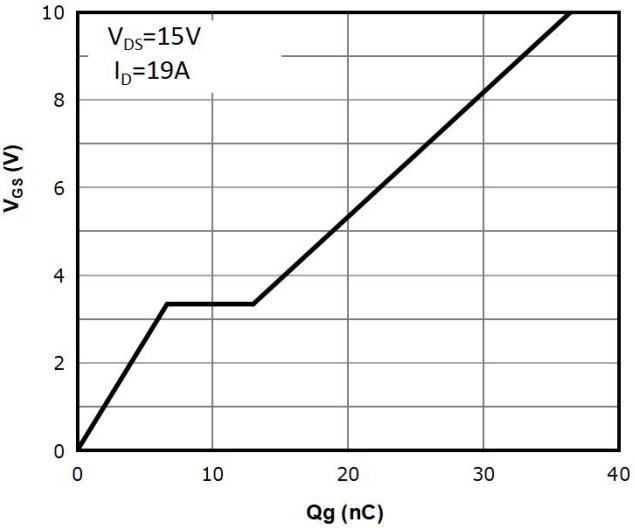


Fig 10: Body-diode Forward Characteristics

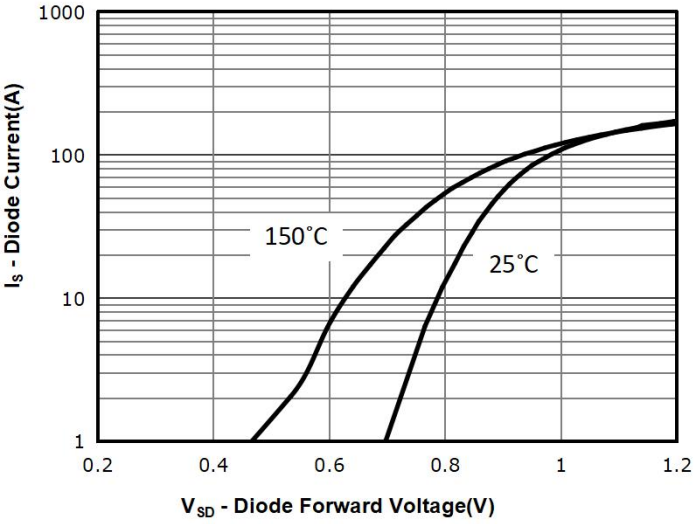


Fig 11: Power Dissipation

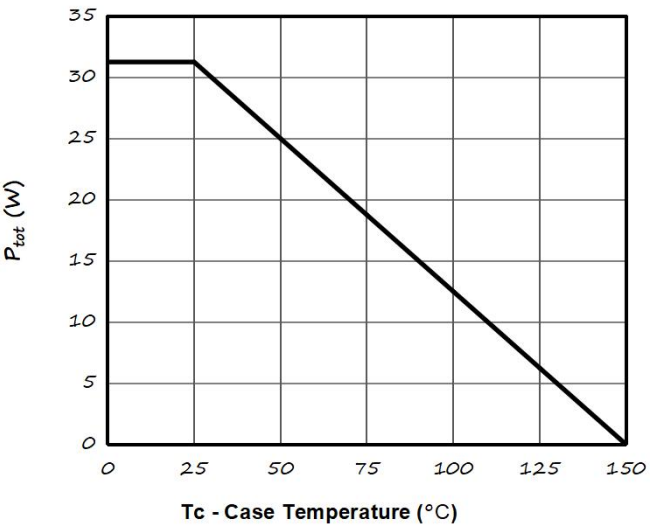


Fig 12: Drain Current Derating

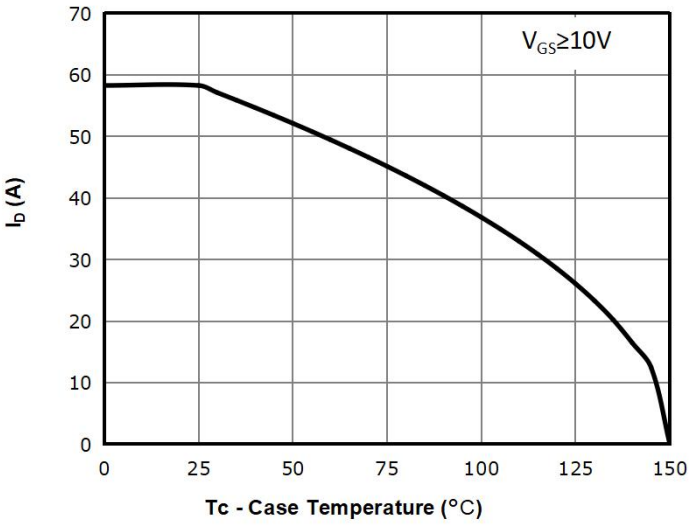


Fig 13: Safe Operating Area

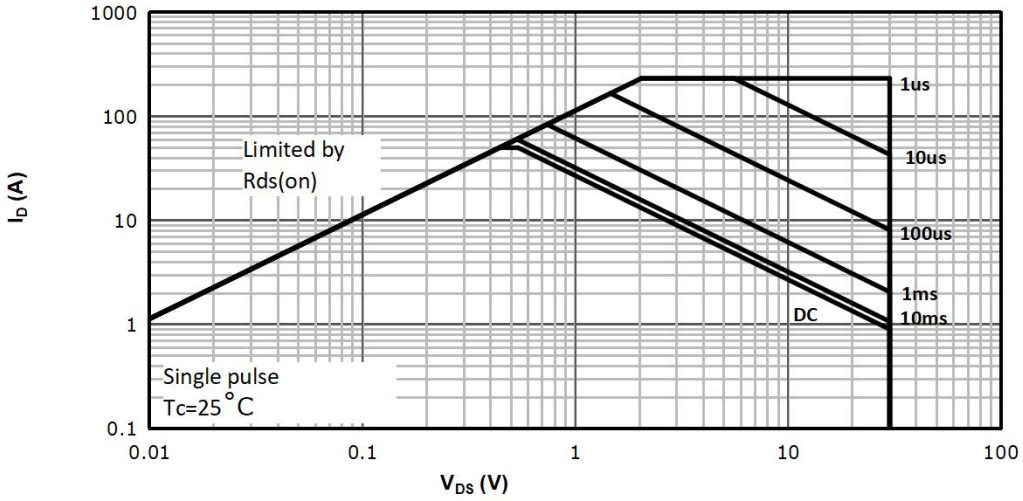
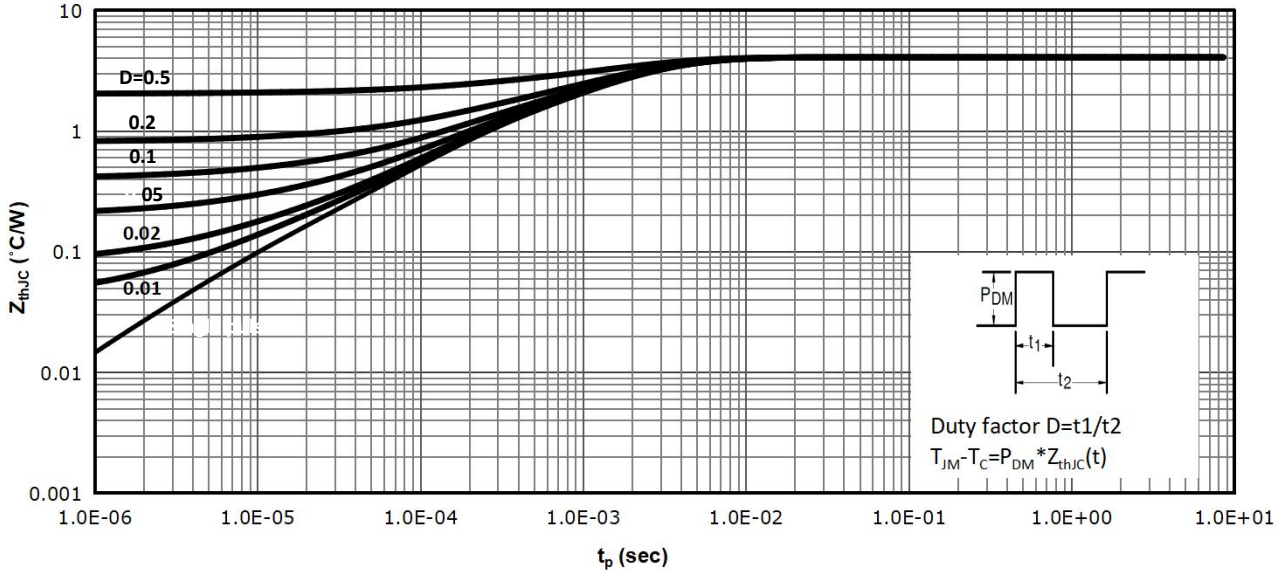
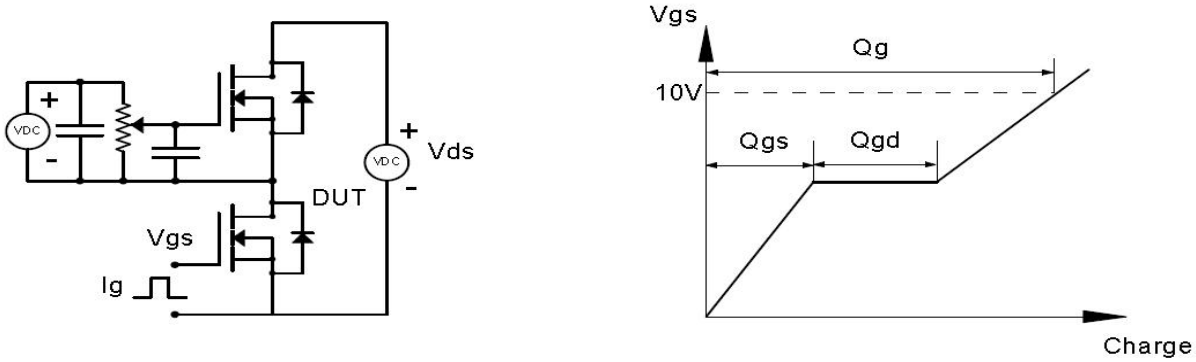


Fig 14: Max. Transient Thermal Impedance

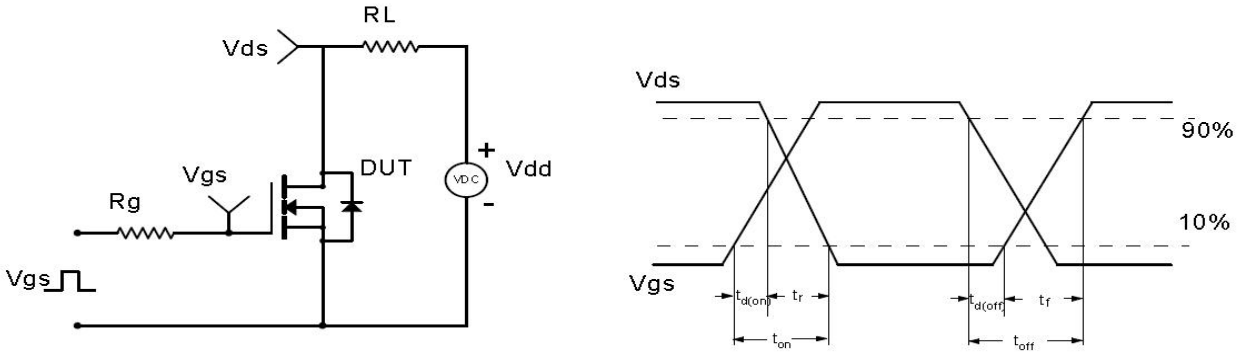


Test Circuit & Waveform

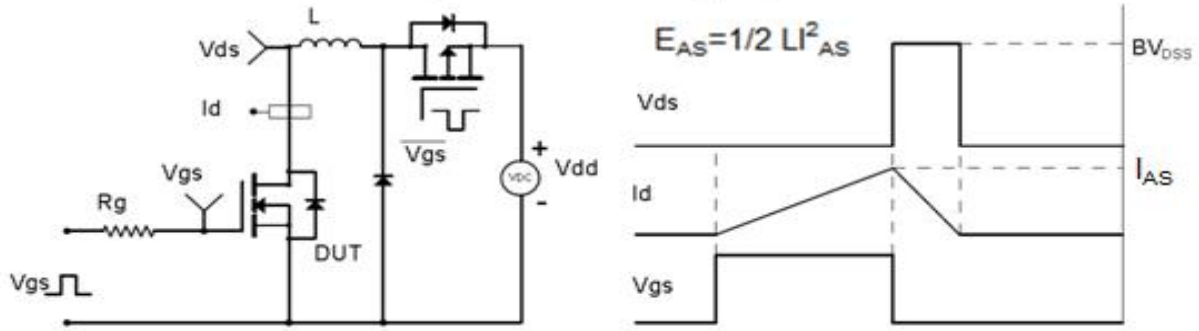
Gate Charge Test Circuit & Waveform



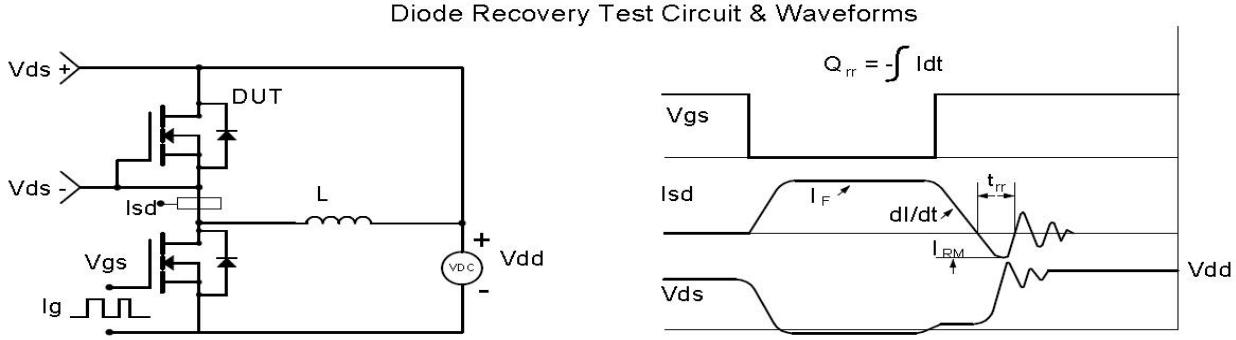
Resistive Switching Test Circuit & Waveforms



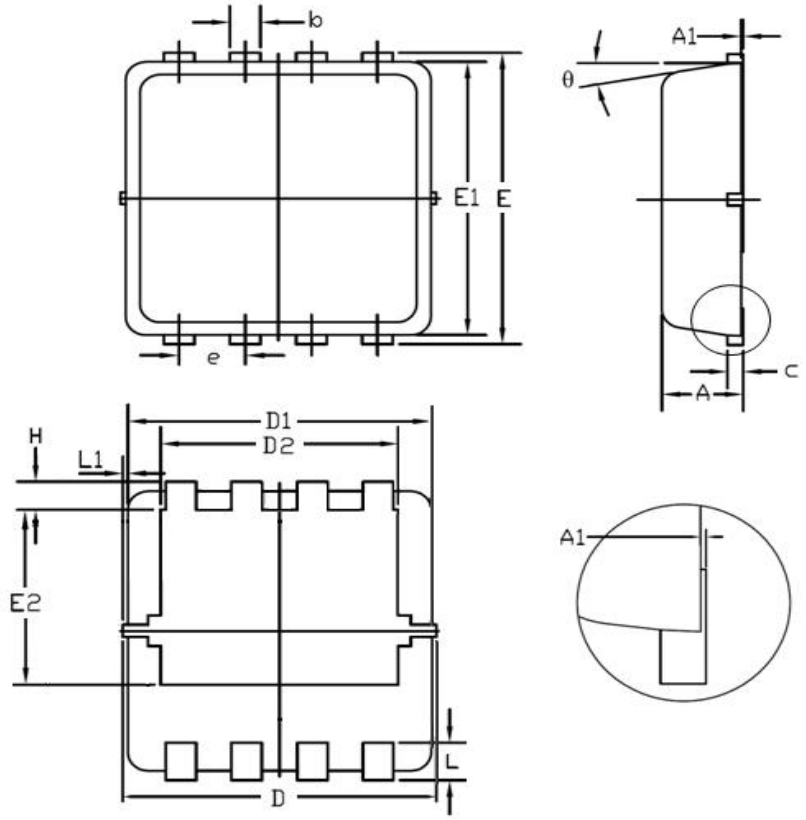
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: PDFN3.3×3.3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.20	0.43	0.008	0.017
c	0.10	0.25	0.004	0.010
D	3.00	3.45	0.118	0.136
D1	2.90	3.30	0.114	0.130
D2	1.98	2.65	0.078	0.104
E	3.10	3.45	0.122	0.136
E1	2.80	3.20	0.110	0.126
E2	1.32	1.98	0.052	0.078
e	0.65 BSC		0.026 BSC	
H	0.28	0.65	0.011	0.026
L	0.30	0.65	0.012	0.026
L1	0.13		0.005	
θ	0°	14°	0°	14°

Marking



NOTE:
XBBAAA

X	—Assembly location code
BB	—Fab code
AAA	—Lot code

Revision History

Revision	Date	Major changes
1.0	2025/6/18	Release of Preliminary version.
2.0	2025/9/11	Modify package information

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.